

TERAHERTZ OPTICAL HALL EFFECT IN AlScN/GaN AND AlYN/GaN HEMT STRUCTURES

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AlGa_N/Ga_N high-electron-mobility transistors (HEMT) have enabled breakthroughs in high-power and high-frequency electronics. AlSc_N and AlY_N provide a higher polarization gradient than AlGa_N and hence increased sheet charge carrier density (n_s) of the two-dimensional electron gas (2DEG) if employed as barrier layers.

Here, we report THz Optical Hall effect (OHE) in AlSc_N/Ga_N and AlY_N/Ga_N HEMT structures, which allow for contactless determination of the 2DEG properties. The samples have ~10-nm thick barrier layers with Sc and Y content of 4.6-17.3% and 3.3-8.2%, respectively. (2) The OHE measurements were performed at magnetic field $B=2.82\text{T}$ and temperatures $T=10-370\text{K}$. The room temperature (RT) OHE results reveal high $n_s=3-3.5 \times 10^{13}\text{cm}^{-2}$ for all Sc contents and mobility parameters of $520-600\text{V(s.cm)}^{-1}$. For the AlY_N HEMT structures the mobility was found to be slightly higher, but for a lower n_s in the range $2-3 \times 10^{13}\text{cm}^{-2}$. These results are corroborated by eddy-current sheet resistance and contactless Hall measurements.

The 2DEG electron effective mass parameters (m^*) was determined at RT to be $m^*=0.34m_0$ for the AlSc_N/Ga_N HEMT structures, in agreement with results for AlGa_N/Ga_N HEMTs. (1,3) For AlY_N barrier structures, the RT 2DEG effective mass was determined to be significantly higher: $0.47m_0$. The analysis of the low temperatures (10-130K) OHE yielded 2DEG effective mass $m^*=0.23-0.27m_0$, much closer to the typically accepted value $m^*=0.23m_0$ for bulk Ga_N. (4) The causes for the peculiar behavior of the 2DEG effective mass are discussed in detail and possible explanation, associated with deviation from the classical Drude model is proposed.